



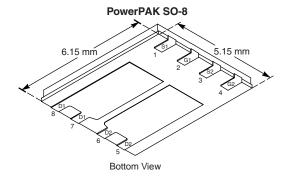
Dual N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)	Q _g (Typ.)			
60	0.023 at V _{GS} = 10 V	9.6	43			

FEATURES

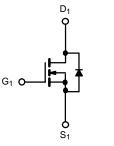
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®] Package
- · Dual MOSFET for Space Savings
- 100 % R_g Tested
- · High Threshold Voltage at High Temperature



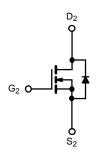


Ordering Information: Si7964DP-T1-E3 (Lead (Pb)-free)

Si7964DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



N-Channel	MOSFET
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Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	60		V
Gate-Source Voltage		V_{GS}	± 20		V
Continuous Drain Current /T 150 °C\8	T _A = 25 °C	I _D	9.6	6.1	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		7.7	4.9	
Pulsed Drain Current		I _{DM}	40		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.2	
Single Avalanche Current	L = 0.1 mH	I _{AS}	25		
Single Avalanche Energy		E _{AS}	31		mJ
Maniana Danian Dianian Manian A	T _A = 25 °C	P _D	3.5	1.4	W
Maximum Power Dissipation ^a	T _A = 70 °C		2.2	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature)b, c		·	260		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	- R _{thJA}	26	35	°C/W
Maximum Junction-to-Ambient	Steady State		60	85	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	2.2	2.7	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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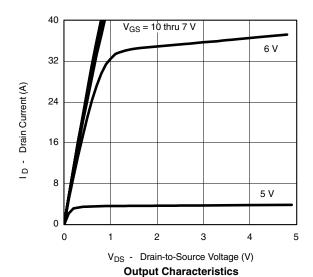
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.4		4.5	٧	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 55 °C			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 9.6 \text{ A}$		0.019	0.023	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 9.6 A		30		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.8	1.2	٧	
Dynamic ^b					•		
Total Gate Charge	Q_g			43	65	nC	
Gate-Source Charge	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 9.6 \text{ A}$		15			
Gate-Drain Charge	Q_{gd}			8.5			
Gate Resistance	R_g	f = 1 MHz	1	2	3	Ω	
Turn-On Delay Time	t _{d(on)}			20	30		
Rise Time	t _r	V_{DD} = 20 V, R_L = 20 Ω		15	25	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		50	75		
Fall Time	t _f			15	25		
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.9 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		35	60		

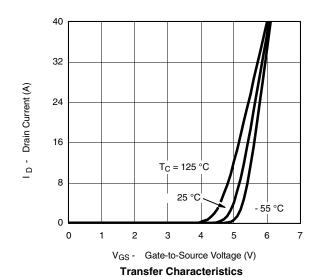
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



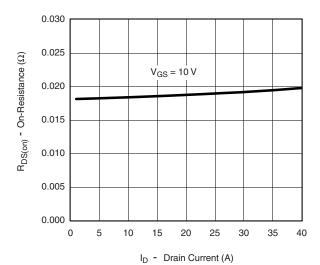




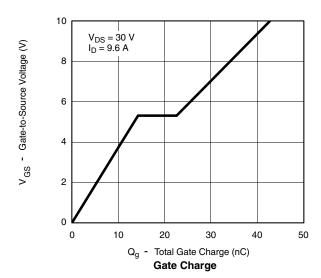


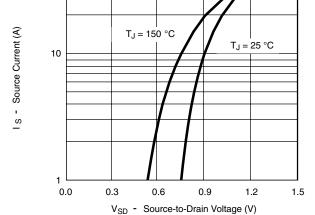


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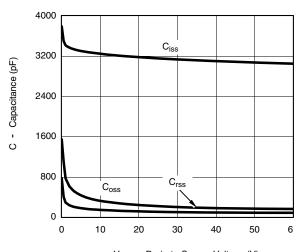


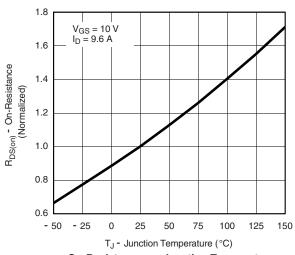
On-Resistance vs. Drain Current



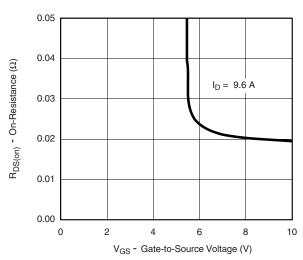


Source-Drain Diode Forward Voltage





On-Resistance vs. Junction Temperature



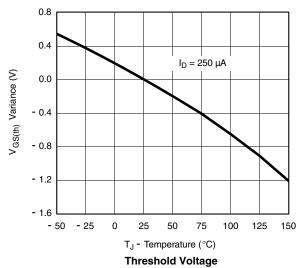
On-Resistance vs. Gate-to-Source Voltage

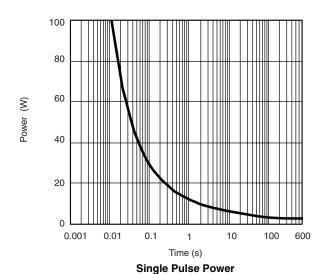
40

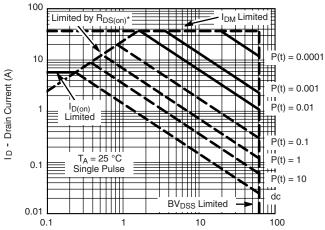
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

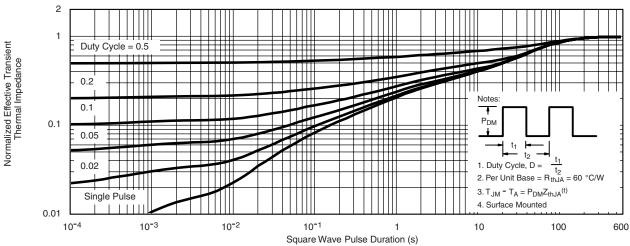






 $\label{eq:VDS} V_{DS} - Drain-to-Source Voltage (V) $$^*V_{GS}$ > minimum V_{GS} at which $R_{DS(on)}$ is specified$

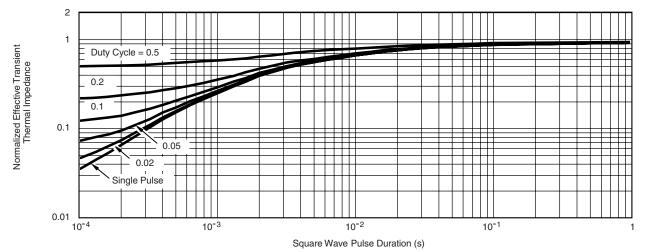
Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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